Ordering number:ENN6362

N-Channel Silicon MOSFET

3LN02C

Ultrahigh-Speed Switching Applications

Features

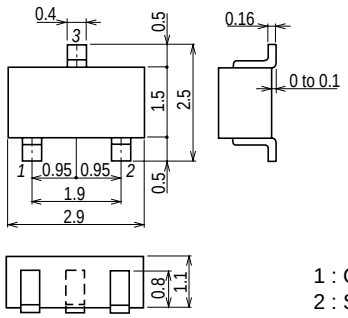
- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit:mm

2091A

[3LN02C]



1 : Gate
2 : Source
3 : Drain
SANYO : CP

Specifications

Absolute Maximum Ratings at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		0.3	A
Drain Current (pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	1.2	A
Allowable Power Dissipation	P_D		0.25	W
Channel Temperature	Tch		150	˚C
Storage Temperature	Tstg		–55 to +150	˚C

Electrical Characteristics at Ta = 25˚C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0			10	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	$V_{GS(off)}$	V_{DS}=10V, I_D=100μA	0.4		1.3	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=150mA	0.4	0.56		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}1$	I_D=150mA, V_{GS}=4V		0.9	1.2	Ω
	$R_{DS(on)}2$	I_D=80mA, V_{GS}=2.5V		1.2	1.7	Ω
	$R_{DS(on)}3$	I_D=10mA, V_{GS}=1.5V		2.6	5.2	Ω

Marking : YD

Continued on next page.

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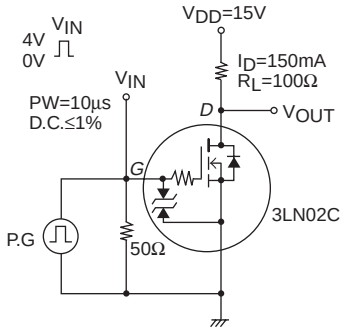
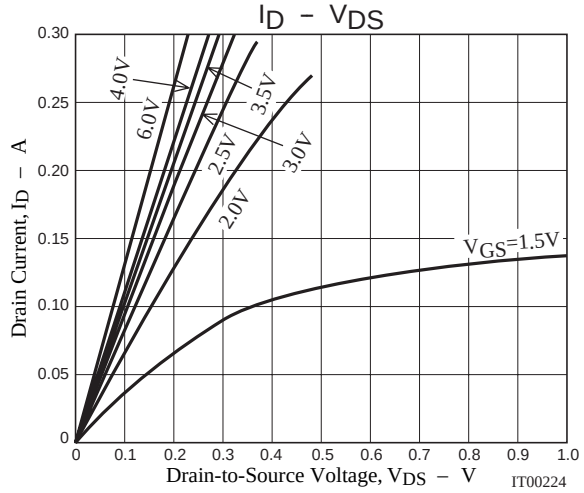
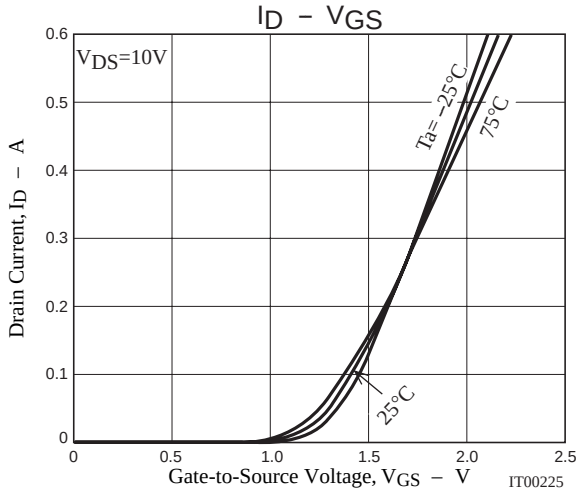
Continued from preceding page.

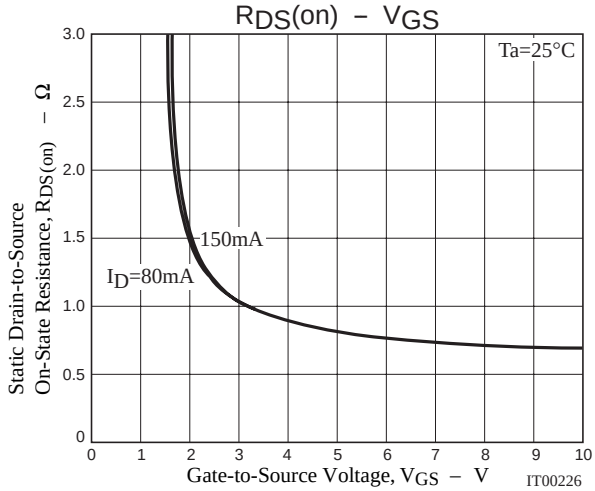
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		30		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		15		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		10		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit		32		ns
Rise Time	t_r	See specified Test Circuit		110		ns
Turn-OFF Delay Time	$t_{d(off)}$	See specified Test Circuit		250		ns
Fall Time	t_f	See specified Test Circuit		160		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=300mA		2.34		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=300mA		0.38		nC
Gate-to-Drain "Miller" Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=300mA		0.45		nC
Diode Forward Voltage	V_{SD}	I_S=300mA, V_{GS}=0		0.8	1.2	V

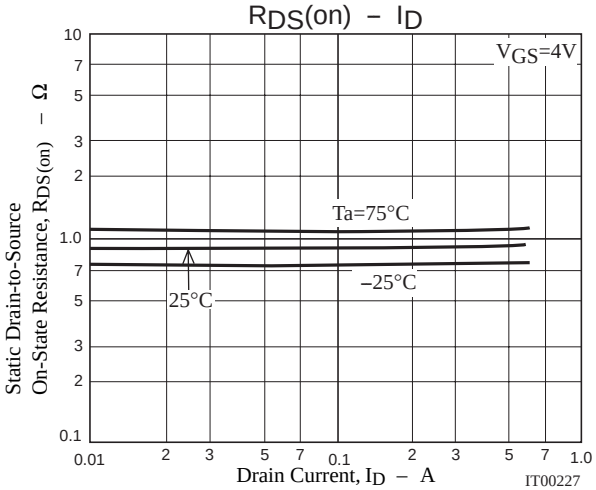
Switching Time Test Circuit

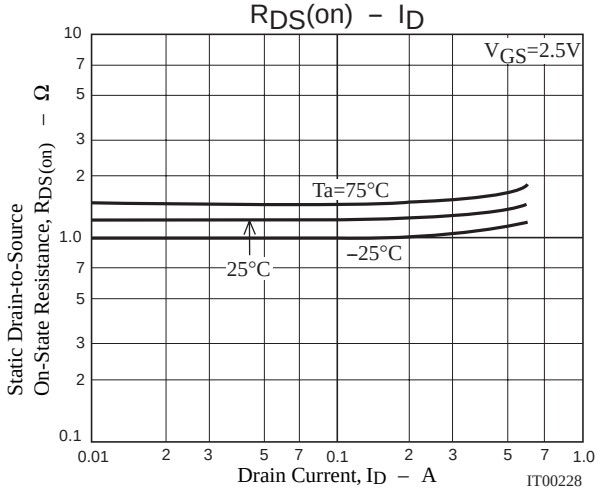


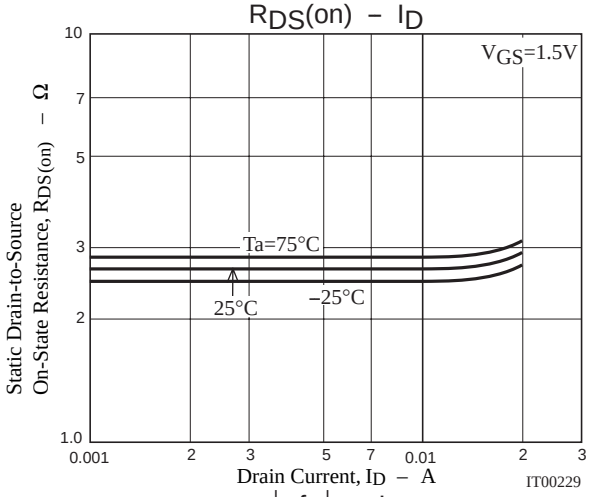


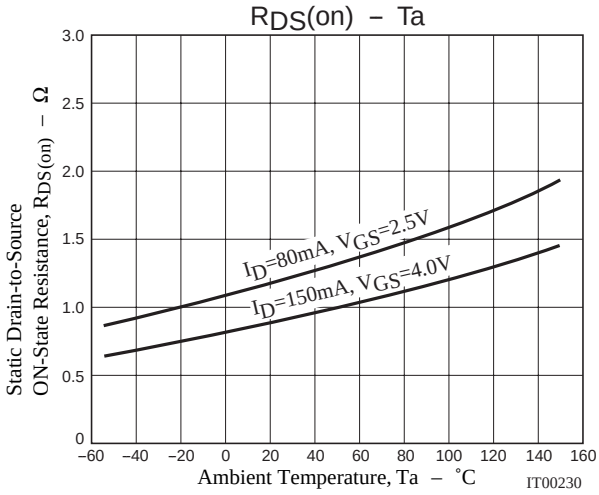


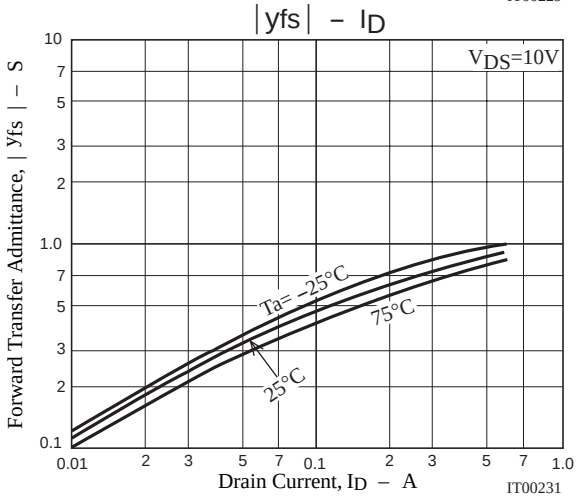


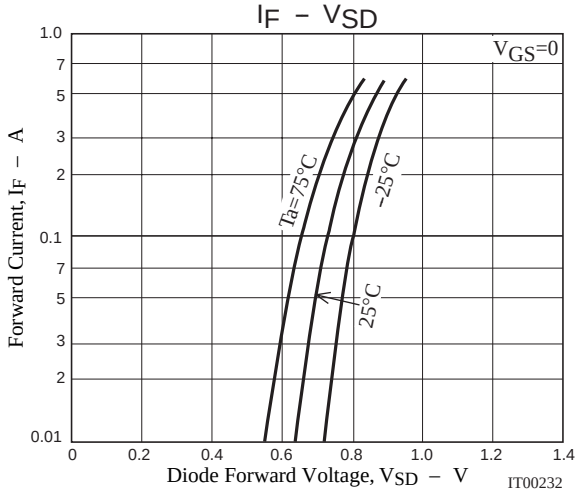


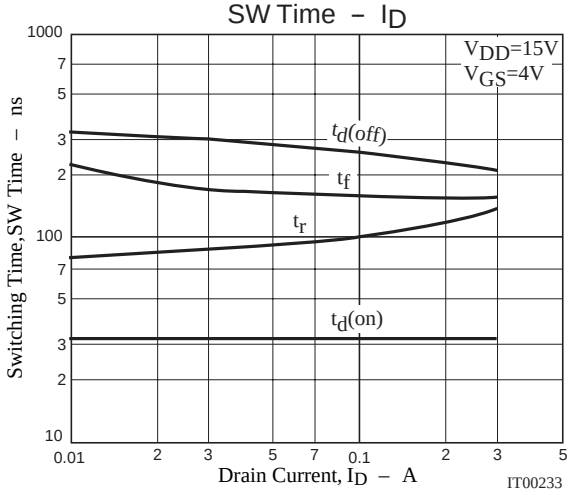

RDS(on) – ID
VGS=2.5V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00228

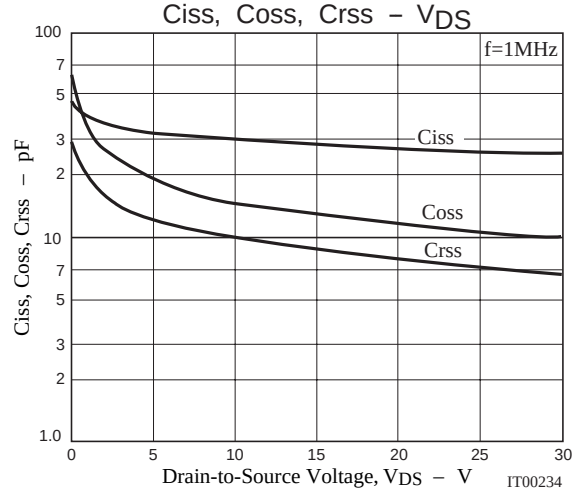

RDS(on) – ID
VGS=1.5V
Ta=75°C
25°C
–25°C
Static Drain-to-Source On-State Resistance, RDS(on) – Ω
Drain Current, ID – A
IT00229

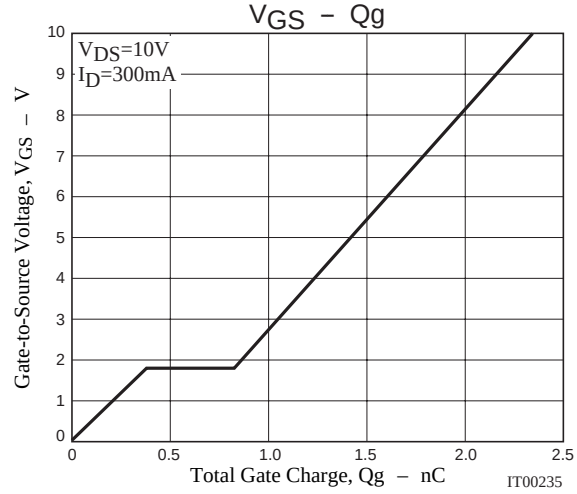

RDS(on) – Ta
ID=80mA, VGS=2.5V
ID=150mA, VGS=4.0V
Static Drain-to-Source ON-State Resistance, RDS(on) – Ω
Ambient Temperature, Ta – °C
IT00230


|yfs| – ID
VDS=10V
Ta= –25°C
75°C
25°C
Forward Transfer Admittance, |Yfs| – S
Drain Current, ID – A
IT00231


IF – VSD
VGS=0
Ta=75°C
–25°C
25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT00232


SW Time – ID
VDD=15V
VGS=4V
td(off)
tf
tr
td(on)
Switching Time, SW Time – ns
Drain Current, ID – A
IT00233


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT00234


VGS – Qg
VDS=10V
ID=300mA
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT00235